

SPTECH Silicon PNP Power Transistor**2SA1141****DESCRIPTION**

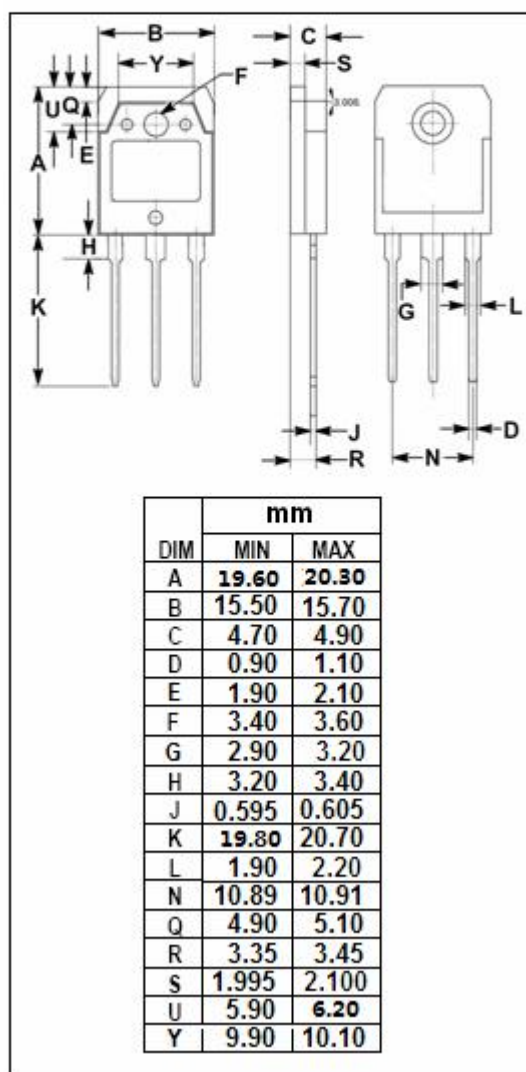
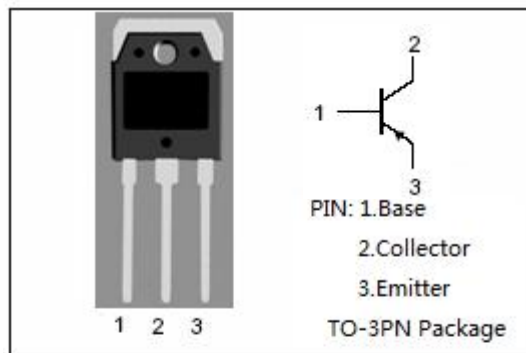
- Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = -115V(\text{Min})$
- Good Linearity of h_{FE}
- Complement to Type 2SC2681

APPLICATIONS

- Audio frequency power amplifier
- High frequency power amplifier

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-115	V
V_{CEO}	Collector-Emitter Voltage	-115	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Peak	-15	A
P_C	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	2.0	W
	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	100	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



SPTECH Silicon PNP Power Transistor**2SA1141****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -4.5A; I _B = -0.45A			-1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -4.5A; V _{CE} = -2V			-2.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -80V; I _E = 0			-50	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-50	μ A
h _{FE-1}	DC Current Gain	I _C = -1A; V _{CE} = -2V	60		200	
h _{FE-2}	DC Current Gain	I _C = -4.5A; V _{CE} = -2V	40			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1.0MHz		390		pF
f _T	Current-Gain—Bandwidth Product	I _C = -1A; V _{CE} = -2V		90		MHz

◆ **h_{FE-1} Classifications**

R	Q
60-120	100-200